

QDLASER

QLD103E-xx50

1030 / 1064 nm >50mW DFB Laser TO-CAN

C00144-02 July 2016



1. DESCRIPTION

The QLD103E-xx50 is a 1030 / 1064-nm distributed feedback (DFB) laser suitable for various applications, such as seeder, measurement, sensing, frequency doubling and etc. The laser is mounted into a TO-56 header including a monitor PD for optical power control and hermetic sealed with a flat type cap.

2. FEATURES

- Single longitudinal mode operation at 1030 nm and 1064 nm
- CW and short pulsed operation
- $\Phi 5.6\text{mm}$ TO-CAN package
- Monitor PD included

3. APPLICATIONS

- Seeder
- Measurement
- Sensing
- Frequency doubling
- Short pulse generation

4. ABSOLUTE MAXIMUM RATINGS

($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Optical Output power	P_O	60	mW
LD Forward Current	I_F	180	mA
LD Reverse Voltage	V_{RLD}	2	V
PD Forward Current	I_{FPD}	2	mA
PD Reverse Voltage	V_{RPD}	10	V
Operation Temperature	T_c	15 to 45	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 85	$^\circ\text{C}$
Lead Soldering Temperature (10 s)	T_{sld}	260	$^\circ\text{C}$

Distributed by  IMM photonics

Ohmstrasse 4, 85716 Unterschleissheim, Germany

www.imm-photonics.de sales@imm-photonics.de Tel.: +49 89 / 3214120

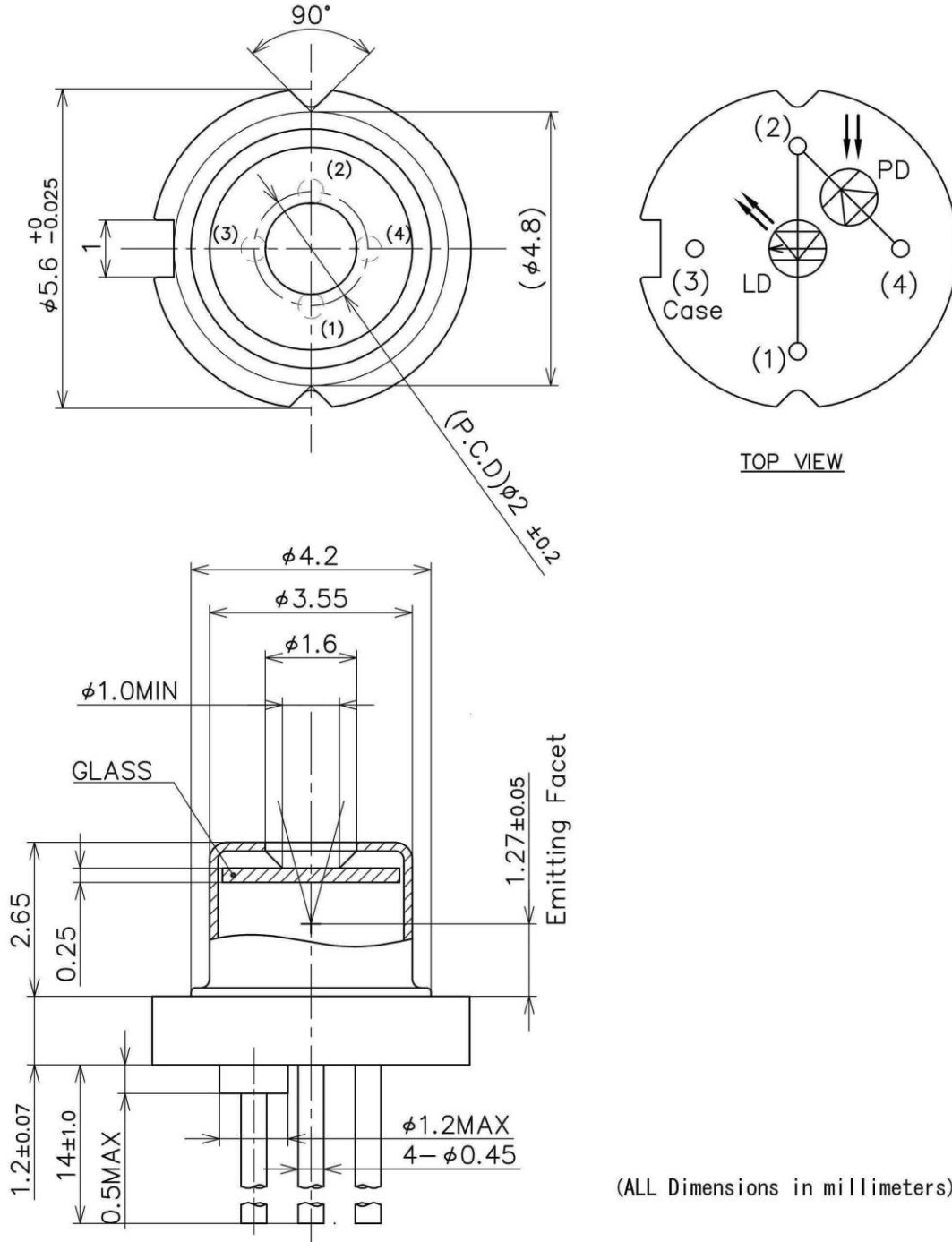
5. OPTICAL AND ELECTRICAL CHARACTERISTICS

(T_{LD} = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Peak Wavelength	QLD103E-6450	λ_p	CW, P _O =50 mW	1059*	1064	1069*	nm
	QLD103E-3050			1025*	1030	1035*	nm
Temperature Coefficient of λ_p		$d\lambda_p/dT$	CW	-	0.08	-	nm/K
Current Coefficient of λ_p		$d\lambda_p/dI$	CW	-	0.008	-	nm/mA
Optical Output Power		P _O	CW	50	-	-	mW
Threshold Current		I _{th}	CW	-	20	-	mA
Operation Current		I _{op}	CW, P _O =50 mW	-	100	150	mA
Operation Voltage		V _{op}	CW, P _O =50 mW	-	1.5	2.0	V
Sidemode Suppression Ratio		SMSR	CW, P _O =50 mW	-	40	-	dB
Far filed pattern horizontal		θ_h	CW, P _O =50 mW	-	10	-	deg.
Far filed pattern vertical		θ_v	CW, P _O =50 mW	-	22	-	deg.
Monitor PD Current		I _m	CW, P _O =50 mW, V _{RPD} =5 V	-	250	-	μA
Dark current (PD)		I _d	V _{RPD} =5 V	-	-	20	nA

*Peak wavelength tolerance of +/- 1nm is available as an option.

6. OUTLINE DRAWING



7. NOTICE

- Safety Information

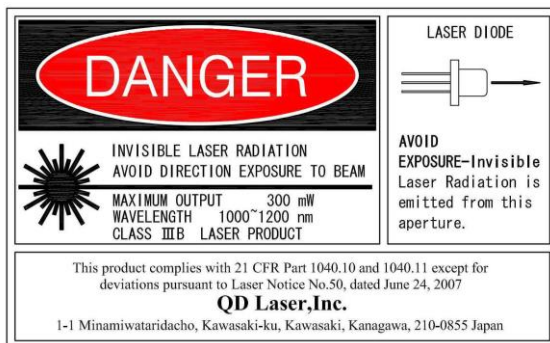
This product is classified as Class 3B laser product, and complies with 21 CFR Part 1040.10. Please do not take a look laser lighting in operations since laser devices may cause troubles to human eyes. Please do not eat, burn, break and make chemical process of the products since they contain GaAs material.

- Handling products

Semiconductor lasers are easily damaged by external stress such as excess temperature and ESD. Please pay attention to handling products, and use within range of maximum ratings. QD Laser takes no responsibility for any failure or unusual operation resulting from improper handling, or unusual physical or electrical stress.

- RoHS

This product conforms to RoHS compliance related EU Directive 2011/65/EU.



Distributed by



Ohmstrasse 4, 85716 Unterschleissheim, Germany

www.imm-photonics.de sales@imm-photonics.de Tel.: +49 89 / 3214120

QD Laser, Inc.

Contact : info@qdlaser.com <http://www.qdlaser.com>

Copyright 2014-2016 All Rights Reserved by QD Laser Inc.

Address : Keihin Bldg. 1F 1-1 Minamiwataridacho, Kawasaki-ku, Kawasaki, Kanagawa Zip 210-0855 Japan

All company or product names mentioned herein are trademarks or registered trademarks of their respective owners. Information provided in this data sheet is accurate at time of publication and is subject to change without advance notice.